

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
20V	250mΩ@4.5V	0.75A
	350mΩ@2.5V	

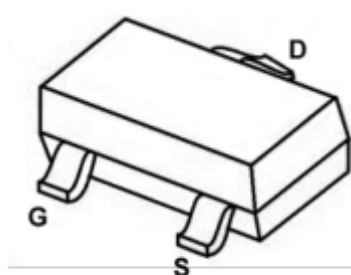
## Feature

- Surface Mount Package
- N-Channel Switch with Low  $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected

## Application

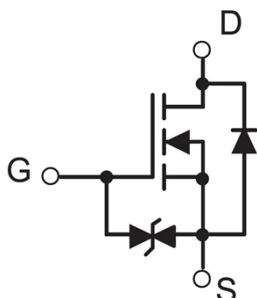
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

## Package

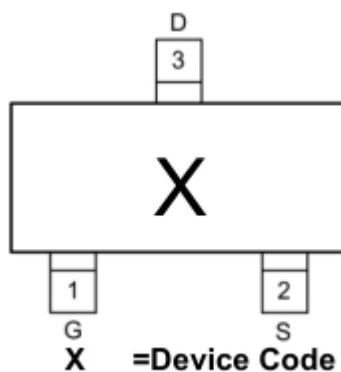


**SOT-523**

## Circuit diagram



## Marking



## Absolute maximum ratings

( $T_a=25^{\circ}\text{C}$  unless otherwise noted)

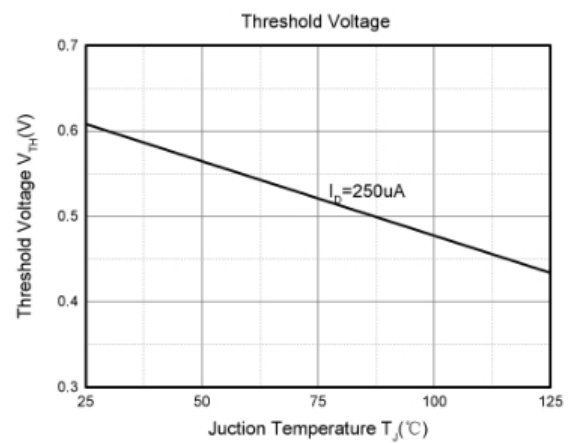
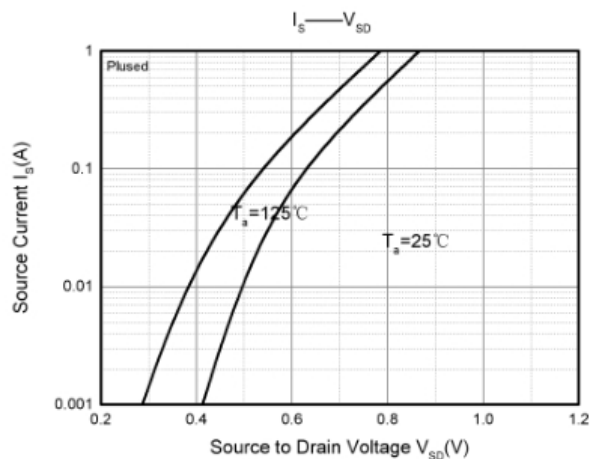
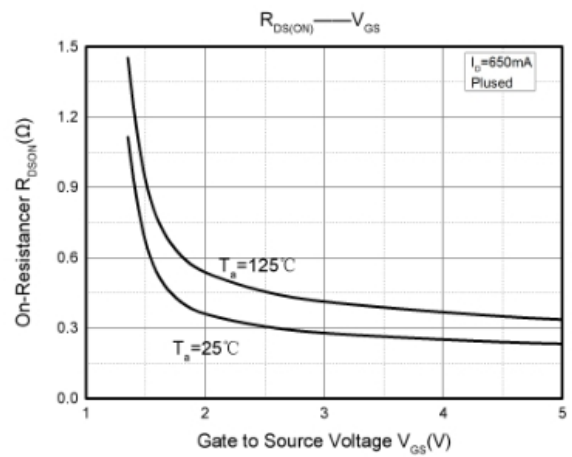
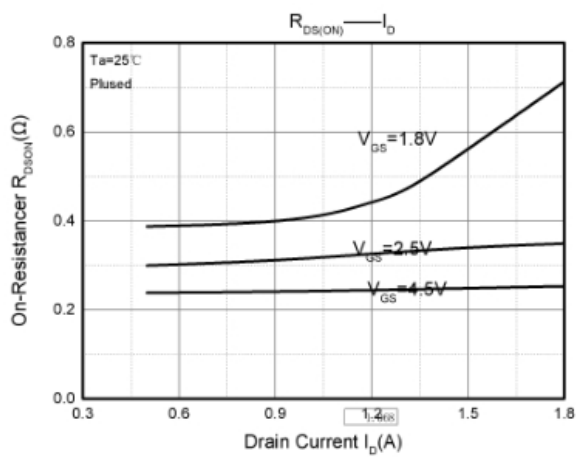
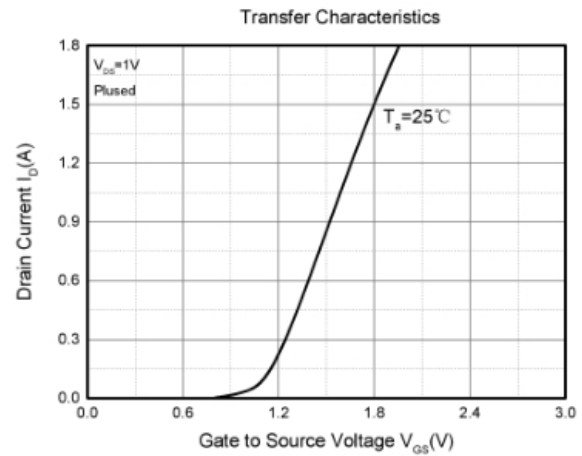
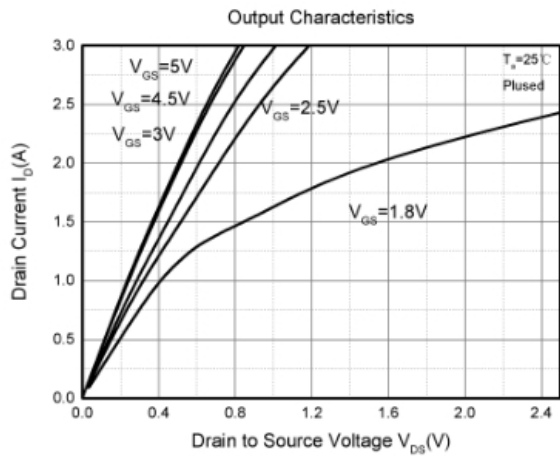
Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 6$	V
Continuous Drain Current	$I_D$	0.75	A
Pulsed Drain Current	$I_{DM}$	3.0	A
Power Dissipation	$P_D$	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}\text{C/W}$
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~ +150	$^{\circ}\text{C}$

## Electrical characteristics

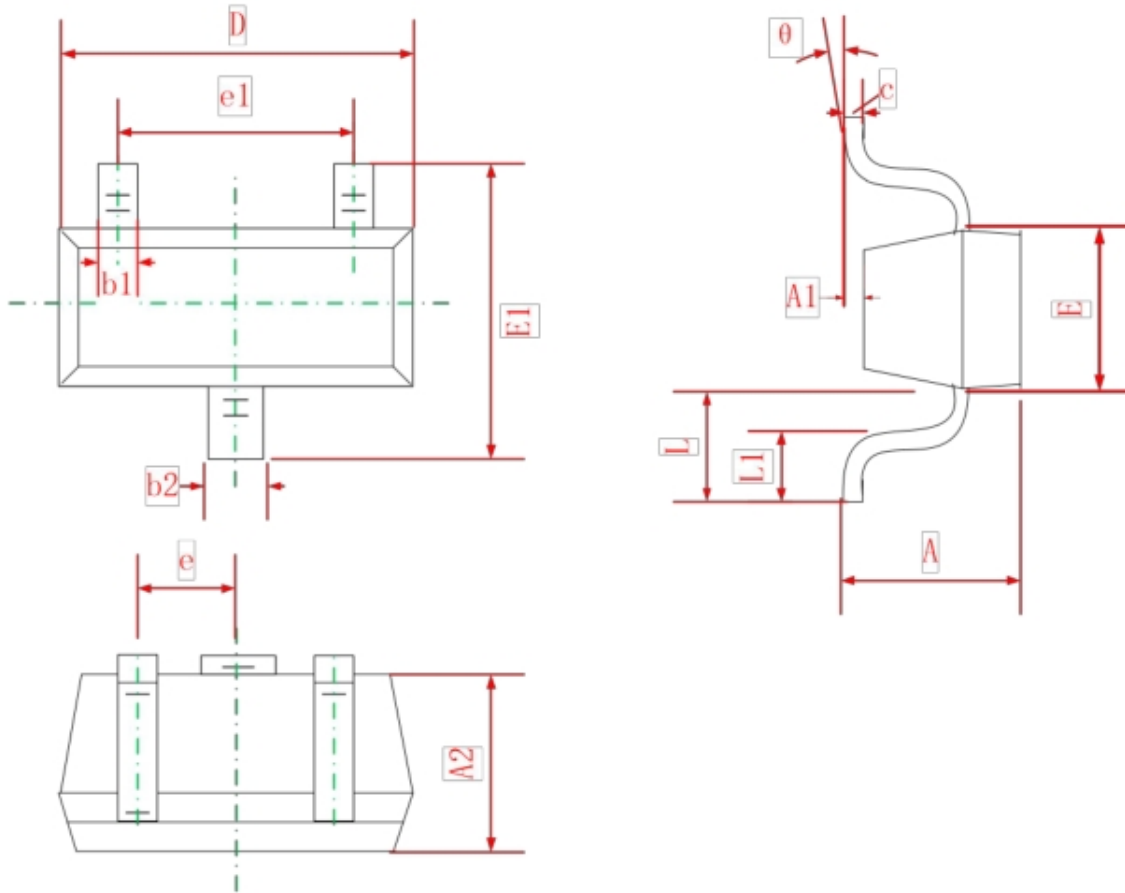
( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> = 0V			100	uA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V			±1	uA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.45	0.65	1.1	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =600mA		250	570	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =500mA		350	620	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =350mA		400	700	
		V <sub>GS</sub> =1.5V, I <sub>D</sub> =40mA			950	
Dynamic Characteristics						
Input capacitance	C <sub>iSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, f=1MHz		79	120	pF
Output capacitance	C <sub>oss</sub>			13	20	
Reverse transfer capacitance	C <sub>rss</sub>			9	15	
Switching Characteristics						
Turn-on Delay Time	T <sub>d(on)</sub>	V <sub>GS</sub> =4.5V, V <sub>DD</sub> =10V, I <sub>D</sub> =500mA , R <sub>GEN</sub> =10Ω		6.7		nS
Turn-on Rise Time	T <sub>r</sub>			4.8		
Turn-Off Delay Time	T <sub>d(off)</sub>			17.3		
Turn-Off Fall Time	t <sub>f</sub>			7.4		
Source-Drain Diode Characteristics						
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> =0.2A, V <sub>GS</sub> =0V			1.2	V

## Typical Characteristics



## SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
$\theta$	0°	8°